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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, I²C, IrDA, LINbus, QSPI, SAI, SPI, SWPMI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, PWM, WDT
Number of I/O	39
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 10x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-UFQFN Exposed Pad
Supplier Device Package	48-UFQFPN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l431ccu6tr

Table 4. Functionalities depending on the working mode[1] (continued)

Peripheral	Run	Sleep	Low-power run	Low-power sleep	Stop 0/1		Stop 2		Standby		Shutdown		VBAT
					-	Wakeup capability	-	Wakeup capability	-	Wakeup capability	-	Wakeup capability	
Low-power UART (LPUART)	O	O	O	O	O[6]	O[6]	O[6]	O[6]	-	-	-	-	-
I2Cx (x=1,2)	O	O	O	O	O[7]	O[7]	-	-	-	-	-	-	-
I2C3	O	O	O	O	O[7]	O[7]	O[7]	O[7]	-	-	-	-	-
SPIx (x=1,2,3)	O	O	O	O	-	-	-	-	-	-	-	-	-
CAN	O	O	O	O	-	-	-	-	-	-	-	-	-
SDMMC1	O	O	O	O	-	-	-	-	-	-	-	-	-
SWPMI1	O	O	O	O	-	O	-	-	-	-	-	-	-
SAIx (x=1)	O	O	O	O	-	-	-	-	-	-	-	-	-
ADCx (x=1)	O	O	O	O	-	-	-	-	-	-	-	-	-
DACx (x=1,2)	O	O	O	O	O	-	-	-	-	-	-	-	-
VREFBUF	O	O	O	O	O	-	-	-	-	-	-	-	-
OPAMPx (x=1)	O	O	O	O	O	-	-	-	-	-	-	-	-
COMPx (x=1,2)	O	O	O	O	O	O	O	O	-	-	-	-	-
Temperature sensor	O	O	O	O	-	-	-	-	-	-	-	-	-
Timers (TIMx)	O	O	O	O	-	-	-	-	-	-	-	-	-
Low-power timer 1 (LPTIM1)	O	O	O	O	O	O	O	O	-	-	-	-	-
Low-power timer 2 (LPTIM2)	O	O	O	O	O	O	-	-	-	-	-	-	-
Independent watchdog (IWDG)	O	O	O	O	O	O	O	O	O	O	-	-	-
Window watchdog (WWDG)	O	O	O	O	-	-	-	-	-	-	-	-	-
SysTick timer	O	O	O	O	-	-	-	-	-	-	-	-	-
Touch sensing controller (TSC)	O	O	O	O	-	-	-	-	-	-	-	-	-
Random number generator (RNG)	O[8]	O[8]	-	-	-	-	-	-	-	-	-	-	-

Figure 3. Clock tree

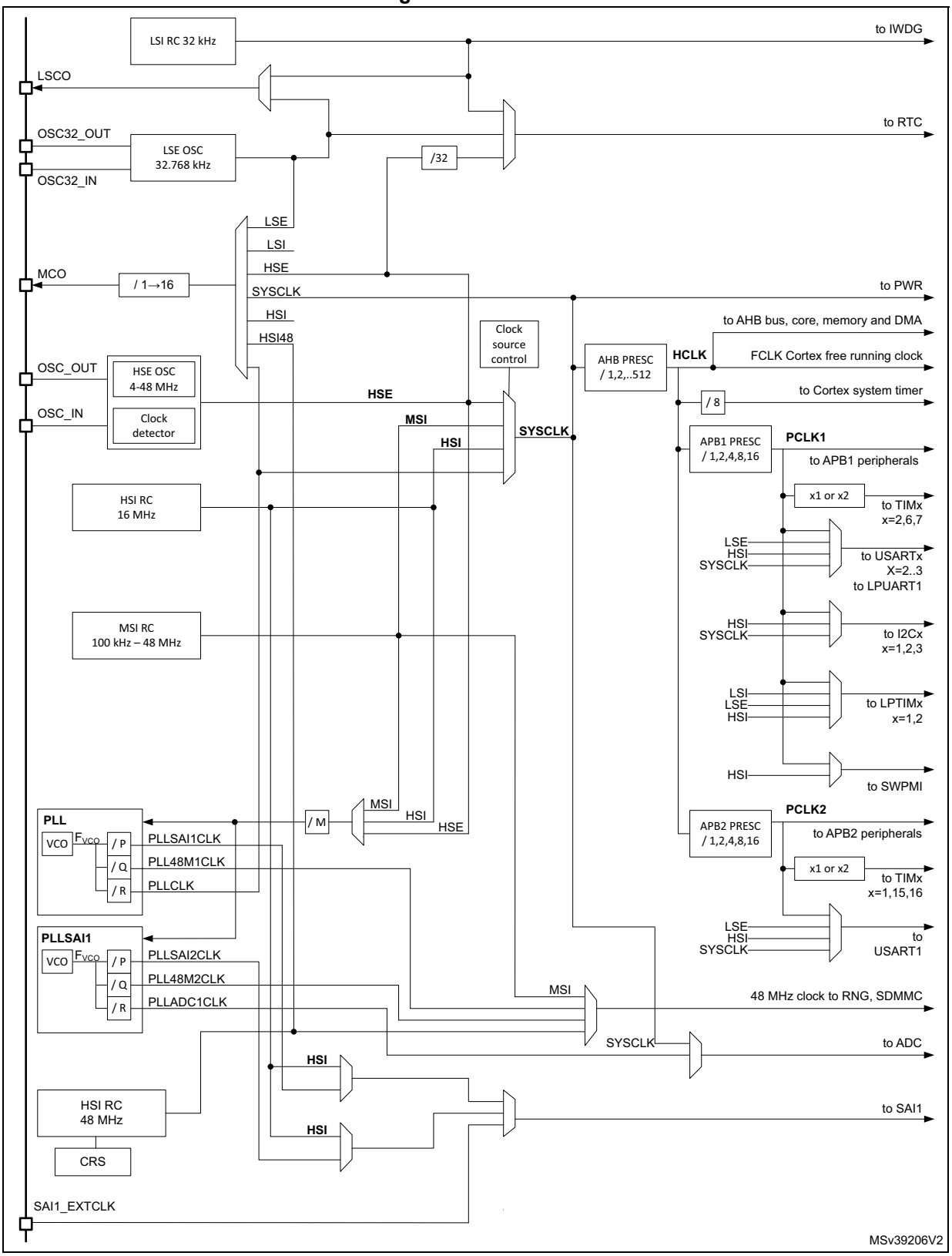


Table 14. STM32L431xx pin definitions (continued)

Pin Number									Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
UFQFPN32	LQFP48	UFQFPN48	WLCSP49	WLCSP64	LQFP64	UFBGA64	LQFP100	UFBGA100					Alternate functions	Additional functions
8	12	12	E5	F6	16	F3	25	K3	PA2	I/O	FT_a	-	TIM2_CH3, USART2_TX, LPUART1_TX, QUADSPI_BK1_NCS, COMP2_OUT, TIM15_CH1, EVENTOUT	COMP2_INM, ADC1_IN7, WKUP4, LSCO
9	13	13	E4	G6	17	G3	26	L3	PA3	I/O	TT_a	-	TIM2_CH4, USART2_RX, LPUART1_RX, QUADSPI_CLK, SAI1_MCLK_A, TIM15_CH2, EVENTOUT	OPAMP1_ VOUT, COMP2_INP, ADC1_IN8
-	-	-	-	H8	18	C2	27	E3	VSS	S	-	-	-	-
-	-	-	-	H7	19	D2	28	H3	VDD	S	-	-	-	-
10	14	14	G6	E5	20	H3	29	M3	PA4	I/O	TT_a	-	SPI1_NSS, SPI3_NSS, USART2_CK, SAI1_FS_B, LPTIM2_OUT, EVENTOUT	COMP1_INM, COMP2_INM, ADC1_IN9, DAC1_OUT1
11	15	15	F5	F5	21	F4	30	K4	PA5	I/O	TT_a	-	TIM2_CH1, TIM2_ETR, SPI1_SCK, LPTIM2_ETR, EVENTOUT	COMP1_INM, COMP2_INM, ADC1_IN10, DAC1_OUT2
12	16	16	F4	G5	22	G4	31	L4	PA6	I/O	FT_a	-	TIM1_BKIN, SPI1_MISO, COMP1_OUT, USART3_CTS, LPUART1_CTS, QUADSPI_BK1_IO3, TIM1_BKIN_COMP2, TIM16_CH1, EVENTOUT	ADC1_IN11
13	17	17	F3	H6	23	H4	32	M4	PA7	I/O	FT_fa	-	TIM1_CH1N, I2C3_SCL, SPI1_MOSI, QUADSPI_BK1_IO2, COMP2_OUT, EVENTOUT	ADC1_IN12
-	-	-	-	D4	24	H5	33	K5	PC4	I/O	FT_a	-	USART3_TX, EVENTOUT	COMP1_INM, ADC1_IN13
-	-	-	-	E4	25	H6	34	L5	PC5	I/O	FT_a	-	USART3_RX, EVENTOUT	COMP1_INP, ADC1_IN14, WKUP5

Table 15. Alternate function AF0 to AF7 (for AF8 to AF15 see *Table 16*)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		SYS_AF	TIM1/TIM2/ LPTIM1	TIM1/TIM2	USART2	I2C1/I2C2/I2C3	SPI1/SPI2	SPI3	USART1/ USART2/ USART3
Port A	PA0	-	TIM2_CH1	-	-	-	-	-	USART2_CTS
	PA1	-	TIM2_CH2	-	-	I2C1_SMBA	SPI1_SCK	-	USART2_RTS_ DE
	PA2	-	TIM2_CH3	-	-	-	-	-	USART2_TX
	PA3	-	TIM2_CH4	-	-	-	-	-	USART2_RX
	PA4	-	-	-	-	-	SPI1_NSS	SPI3_NSS	USART2_CK
	PA5	-	TIM2_CH1	TIM2_ETR	-	-	SPI1_SCK	-	-
	PA6	-	TIM1_BKIN	-	-	-	SPI1_MISO	COMP1_OUT	USART3_CTS
	PA7	-	TIM1_CH1N	-	-	I2C3_SCL	SPI1_MOSI	-	-
	PA8	MCO	TIM1_CH1	-	-	-	-	-	USART1_CK
	PA9	-	TIM1_CH2	-	-	I2C1_SCL	-	-	USART1_TX
	PA10	-	TIM1_CH3	-	-	I2C1_SDA	-	-	USART1_RX
	PA11	-	TIM1_CH4	TIM1_BKIN2	-	-	SPI1_MISO	COMP1_OUT	USART1_CTS
	PA12	-	TIM1_ETR	-	-	-	SPI1_MOSI	-	USART1_RTS_ DE
	PA13	JTMS-SWDIO	IR_OUT	-	-	-	-	-	-
	PA14	JTCK-SWCLK	LPTIM1_OUT	-	-	I2C1_SMBA	-	-	-
	PA15	JTDI	TIM2_CH1	TIM2_ETR	USART2_RX	-	SPI1_NSS	SPI3_NSS	USART3_RTS_ DE

Table 16. Alternate function AF8 to AF15 (for AF0 to AF7 see *Table 15*) (continued)

Port		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		LPUART1	CAN1/TSC	QUADSPI		SDMMC1/ COMP1/ COMP2/ SWPMI1	SAI1	TIM2/TIM15/ TIM16/LPTIM2	EVENTOUT
Port B	PB0	-	-	QUADSPI_ BK1_IO1		COMP1_OUT	SAI1_EXTCLK	-	EVENTOUT
	PB1	LPUART1_RTS _DE	-	QUADSPI_ BK1_IO0		-	-	LPTIM2_IN1	EVENTOUT
	PB2	-	-	-		-	-	-	EVENTOUT
	PB3	-	-	-		-	SAI1_SCK_B	-	EVENTOUT
	PB4	-	TSC_G2_IO1	-		-	SAI1_MCLK_B	-	EVENTOUT
	PB5	-	TSC_G2_IO2	-		COMP2_OUT	SAI1_SD_B	TIM16_BKIN	EVENTOUT
	PB6	-	TSC_G2_IO3	-	-	-	SAI1_FS_B	TIM16_CH1N	EVENTOUT
	PB7	-	TSC_G2_IO4	-		-	-	-	EVENTOUT
	PB8	-	CAN1_RX	-		SDMMC1_D4	SAI1_MCLK_A	TIM16_CH1	EVENTOUT
	PB9	-	CAN1_TX	-		SDMMC1_D5	SAI1_FS_A	-	EVENTOUT
	PB10	LPUART1_RX	TSC_SYNC	QUADSPI_CLK		COMP1_OUT	SAI1_SCK_A	-	EVENTOUT
	PB11	LPUART1_TX	-	QUADSPI_ BK1_NCS		COMP2_OUT	-	-	EVENTOUT
	PB12	LPUART1_RTS _DE	TSC_G1_IO1	-		SWPMI1_IO	SAI1_FS_A	TIM15_BKIN	EVENTOUT
	PB13	LPUART1_CTS	TSC_G1_IO2	-		SWPMI1_TX	SAI1_SCK_A	TIM15_CH1N	EVENTOUT
	PB14	-	TSC_G1_IO3	-		SWPMI1_RX	SAI1_MCLK_A	TIM15_CH1	EVENTOUT
	PB15	-	TSC_G1_IO4	-		SWPMI1_ SUSPEND	SAI1_SD_A	TIM15_CH2	EVENTOUT

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified, the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = 25 °C and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean ±3σ).

6.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = V_{DDA} = 3 V. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean ±2σ).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 15*.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 16*.

Figure 15. Pin loading conditions

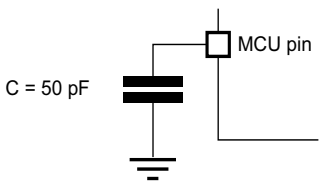


Figure 16. Pin input voltage

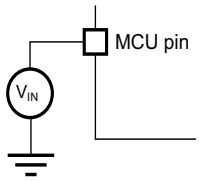


Table 27. Current consumption in Run and Low-power run modes, code with data processing running from SRAM1

Symbol	Parameter	Conditions			TYP					MAX(1)					Unit
		-	Voltage scaling	f_{HCLK}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DD}(Run)	Supply current in Run mode	$f_{HCLK} = f_{HSE}$ up to 48MHz included, bypass mode PLL ON above 48 MHz all peripherals disable	Range 2	26 MHz	2.42	2.43	2.49	2.56	2.71	2.7	2.7	2.8	3.0	3.3	mA
				16 MHz	1.54	1.55	1.6	1.67	1.82	1.7	1.7	1.8	2.0	2.3	
				8 MHz	0.82	0.84	0.88	0.95	1.1	0.9	1.0	1.0	1.2	1.5	
				4 MHz	0.47	0.48	0.52	0.59	0.73	0.5	0.6	0.6	0.8	1.1	
				2 MHz	0.29	0.3	0.34	0.41	0.55	0.3	0.4	0.4	0.6	0.9	
				1 MHz	0.2	0.21	0.25	0.32	0.46	0.2	0.3	0.3	0.5	0.8	
				100 kHz	0.12	0.13	0.17	0.24	0.38	0.1	0.2	0.2	0.4	0.7	
			Range 1	80 MHz	8.63	8.68	8.74	8.84	9.01	9.5	9.6	9.7	9.9	10.2	
				72 MHz	7.79	7.83	7.9	7.99	8.17	8.6	8.6	8.8	8.9	9.3	
				64 MHz	6.95	6.99	7.05	7.15	7.32	7.7	7.7	7.9	8.0	8.4	
				48 MHz	5.19	5.22	5.29	5.38	5.55	5.8	5.8	5.9	6.1	6.5	
				32 MHz	3.51	3.53	3.6	3.68	3.85	3.9	4.0	4.1	4.2	4.6	
				24 MHz	2.66	2.68	2.74	2.83	2.99	3.0	3.0	3.1	3.3	3.6	
				16 MHz	1.82	1.84	1.89	1.98	2.14	2.0	2.1	2.2	2.3	2.7	
I_{DD}(LPRun)	Supply current in low-power run mode	$f_{HCLK} = f_{MSI}$ all peripherals disable FLASH in power-down		2 MHz	205	228	275	352	501	276.5	302.3	358.4	502.5	816.4	µA
				1 MHz	111	126	175	248	397	151.3	180.9	245.3	390.7	703.4	
				400 kHz	49.2	62.7	108	181	330	73.3	104.0	170.8	321.0	632.4	
				100 kHz	21.5	33.3	76.6	151	299	36.4	67.7	137.2	287.8	600.8	

1. Guaranteed by characterization results, unless otherwise specified.

Table 31. Current consumption in Sleep and Low-power sleep modes, Flash ON

Symbol	Parameter	Conditions			TYP					MAX(1)					Unit
		-	Voltage scaling	f_{HCLK}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DD}(Sleep)	Supply current in sleep mode,	$f_{HCLK} = f_{HSE}$ up to 48 MHz included, bypass mode pll ON above 48 MHz all peripherals disable	Range 2	26 MHz	0.68	0.69	0.74	0.81	0.95	0.8	0.8	0.9	1.0	1.3	mA
				16 MHz	0.46	0.48	0.52	0.59	0.73	0.5	0.6	0.6	0.8	1.1	
				8 MHz	0.29	0.30	0.34	0.41	0.55	0.3	0.4	0.4	0.6	0.9	
				4 MHz	0.20	0.21	0.25	0.32	0.46	0.2	0.3	0.3	0.5	0.8	
				2 MHz	0.16	0.17	0.21	0.28	0.42	0.2	0.2	0.3	0.4	0.7	
				1 MHz	0.13	0.15	0.19	0.26	0.40	0.1	0.2	0.3	0.4	0.7	
				100 kHz	0.11	0.13	0.17	0.24	0.38	0.1	0.2	0.2	0.4	0.7	
			Range 1	80 MHz	2.23	2.25	2.30	2.38	2.54	2.5	2.5	2.6	2.8	3.1	
				72 MHz	2.02	2.04	2.10	2.18	2.34	2.2	2.3	2.4	2.5	2.9	
				64 MHz	1.82	1.84	1.89	1.98	2.14	2.0	2.1	2.1	2.3	2.6	
				48 MHz	1.34	1.36	1.42	1.50	1.66	1.5	1.6	1.7	1.8	2.2	
				32 MHz	0.93	0.95	1.01	1.09	1.25	1.1	1.1	1.2	1.4	1.7	
				24 MHz	0.73	0.75	0.80	0.88	1.04	0.8	0.9	1.0	1.1	1.4	
				16 MHz	0.53	0.55	0.60	0.68	0.84	0.6	0.6	0.7	0.9	1.2	
I_{DD}(LPSleep)	Supply current in low-power sleep mode	$f_{HCLK} = f_{MSI}$ all peripherals disable		2 MHz	71.8	80.7	125	200	350	91.1	122.7	191.3	341.5	653.5	µA
				1 MHz	45.0	57.3	101	176	325	63.2	95.4	165.4	316.5	628.7	
				400 kHz	27.0	40.7	84.6	158	308	43.9	75.8	147.2	297.6	609.2	
				100 kHz	22.8	30.9	63.3	113.2	207.7	35.2	67.9	140.9	290.8	602.4	

1. Guaranteed by characterization results, unless otherwise specified.

Table 32. Current consumption in Low-power sleep modes, Flash in power-down

Symbol	Parameter	Conditions			TYP					MAX(1)					Unit
		-	Voltage scaling	f_{HCLK}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DD}(LPSleep)	Supply current in low-power sleep mode	$f_{HCLK} = f_{MSI}$ all peripherals disable		2 MHz	58.7	70.7	103.2	153.7	248.5	80	113	180	330	641	µA
				1 MHz	39.4	47.2	79.3	129.6	224.8	53	86	154	304	616	
				400 kHz	20.8	30.8	62.1	112.5	207.8	35	67	137	286	597	
				100 kHz	14.3	23.1	55.1	105.7	201.5	27	58	130	279	590	

1. Guaranteed by characterization results, unless otherwise specified.

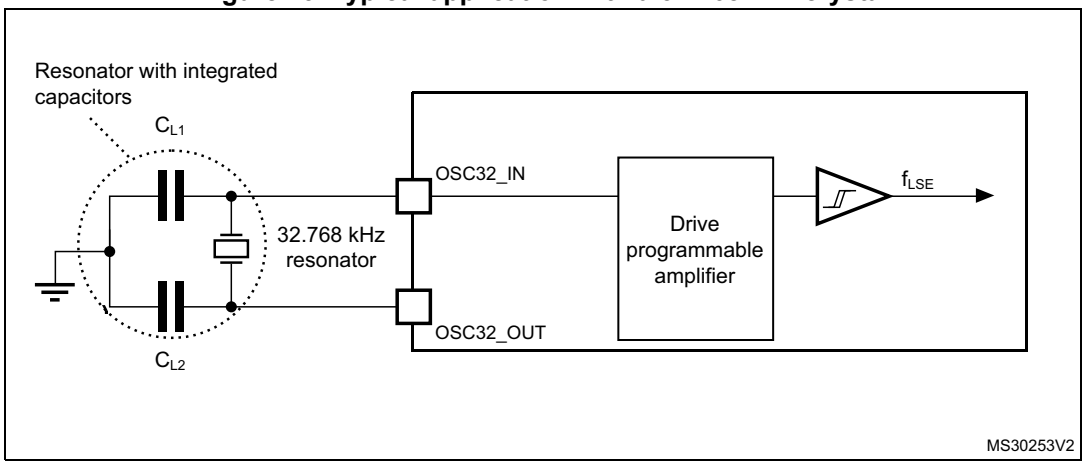
Table 33. Current consumption in Stop 2 mode

Symbol	Parameter	Conditions		TYP					MAX(1)					Unit
		-	V_{DD}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DD} (Stop 2)	Supply current in Stop 2 mode, RTC disabled	-	1.8 V	1	2.54	8.74	19.8	43.4	2.0	5.6	21.1	50.8	116.0	µA
			2.4 V	1.02	2.59	8.89	20.2	44.3	2.1	5.8	21.6	52.3	119.6	
			3 V	1.06	2.67	9.11	20.7	45.5	2.1	5.9	22.2	53.7	123.2	
			3.6 V	1.23	2.88	9.56	21.6	47.3	2.3	6.1	23.0	55.8	127.9	
I_{DD} (Stop 2 with RTC)	Supply current in Stop 2 mode, RTC enabled	RTC clocked by LSI	1.8 V	1.3	2.82	9.02	20.1	43.6	2.5	6.2	21.6	51.3	116.3	µA
			2.4 V	1.39	2.95	9.24	20.5	44.6	2.8	6.4	22.3	52.8	120.0	
			3 V	1.5	3.11	9.55	21.1	45.8	3.0	6.8	23.0	54.5	123.8	
			3.6 V	1.76	3.42	10.1	22.1	47.8	3.3	7.2	24.1	56.7	128.7	
		RTC clocked by LSE bypassed at 32768 Hz	1.8 V	1.36	2.9	9.1	20.1	43.7	-	-	-	-	-	
			2.4 V	1.48	3.09	9.44	20.8	45	-	-	-	-	-	
			3 V	1.83	3.67	10.4	22.3	47.3	-	-	-	-	-	
			3.6 V	3.58	6.17	13.9	26.6	53	-	-	-	-	-	
		RTC clocked by LSE quartz(2) in low drive mode	1.8 V	1.28	2.81	9.13	20.8	-	-	-	-	-	-	
			2.4 V	1.39	2.93	9.34	21.3	-	-	-	-	-	-	
			3 V	1.59	3.1	9.64	21.8	-	-	-	-	-	-	
			3.6 V	1.86	3.45	10.2	22.8	-	-	-	-	-	-	

1. Guaranteed by design.
2. Refer to the note and caution paragraphs below the table, and to the application note AN2867 “Oscillator design guide for ST microcontrollers”.
3. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer

Note: For information on selecting the crystal, refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website www.st.com.

Figure 23. Typical application with a 32.768 kHz crystal



Note: An external resistor is not required between OSC32_IN and OSC32_OUT and it is forbidden to add one.

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 55. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{HCLK}]	Unit
				8 MHz/ 80 MHz	
S_{EMI}	Peak level	V_{DD} = 3.6 V, T_A = 25 °C, LQFP100 package compliant with IEC 61967-2	0.1 MHz to 30 MHz	-8	dBµV
			30 MHz to 130 MHz	2	
			130 MHz to 1 GHz	5	
			1 GHz to 2 GHz	8	
			EMI Level	2.5	-

6.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

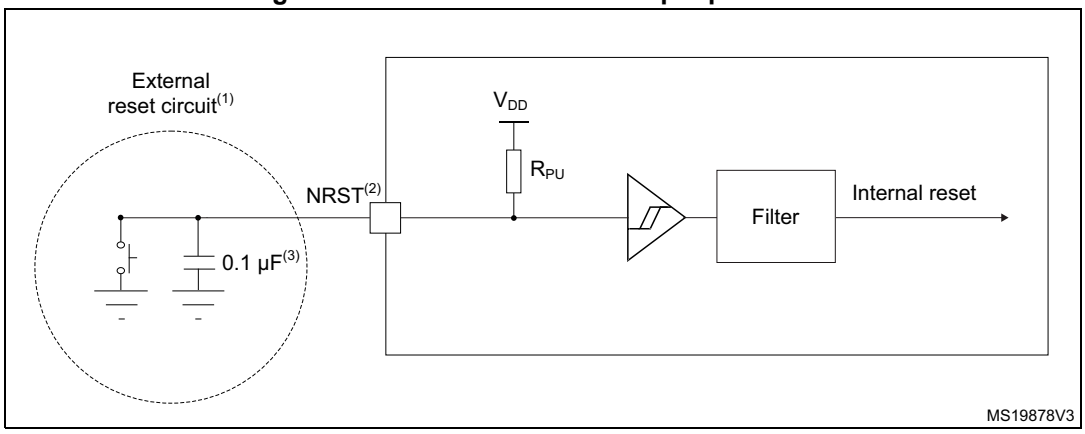
Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the ANSI/JEDEC standard.

Table 56. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C, conforming to ANSI/ESDA/JEDEC JS-001	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C, conforming to ANSI/ESD STM5.3.1	C3	250	

1. Guaranteed by characterization results.

Figure 29. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in *Table 62: NRST pin characteristics*. Otherwise the reset will not be taken into account by the device.
3. The external capacitor on NRST must be placed as close as possible to the device.

6.3.16 Analog switches booster

Table 63. Analog switches booster characteristics(1)

Symbol	Parameter	Min	Typ	Max	Unit
V_{DD}	Supply voltage	1.62	-	3.6	V
$t_{SU(BOOST)}$	Booster startup time	-	-	240	µs
$I_{DD(BOOST)}$	Booster consumption for 1.62 V ≤ V_{DD} ≤ 2.0 V	-	-	250	µA
	Booster consumption for 2.0 V ≤ V_{DD} ≤ 2.7 V	-	-	500	
	Booster consumption for 2.7 V ≤ V_{DD} ≤ 3.6 V	-	-	900	

1. Guaranteed by design.

Table 66. ADC accuracy - limited test conditions 1(1)(2)(3) (continued)

Sym-bol	Parameter	Conditions(4)			Min	Typ	Max	Unit
THD	Total harmonic distortion	ADC clock frequency ≤ 80 MHz, Sampling rate ≤ 5.33 Msps, $V_{DDA} = V_{REF+}$ = 3 V, TA = 25 °C	Single ended	Fast channel (max speed)	-	-74	-73	dB
				Slow channel (max speed)	-	-74	-73	
			Differential	Fast channel (max speed)	-	-79	-76	
				Slow channel (max speed)	-	-79	-76	

1. Guaranteed by design.
2. ADC DC accuracy values are measured after internal calibration.
3. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
4. The I/O analog switch voltage booster is enable when V_{DDA} < 2.4 V (BOOSTEN = 1 in the SYSCFG_CFGR1 when V_{DDA} < 2.4 V). It is disable when V_{DDA} ≥ 2.4 V. No oversampling.

6.3.18 Digital-to-Analog converter characteristics

Table 70. DAC characteristics(1)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage for DAC ON	-		1.8	-	3.6	V
V_{REF+}	Positive reference voltage	-		1.8	-	V_{DDA}	
V_{REF-}	Negative reference voltage	-		V_{SSA}			
R_L	Resistive load	DAC output buffer ON	connected to V_{SSA}	5	-	-	kΩ
			connected to V_{DDA}	25	-	-	
R_O	Output Impedance	DAC output buffer OFF		9.6	11.7	13.8	kΩ
R_{BON}	Output impedance sample and hold mode, output buffer ON	V_{DD} = 2.7 V		-	-	2	kΩ
		V_{DD} = 2.0 V		-	-	3.5	
R_{BOFF}	Output impedance sample and hold mode, output buffer OFF	V_{DD} = 2.7 V		-	-	16.5	kΩ
		V_{DD} = 2.0 V		-	-	18.0	
C_L	Capacitive load	DAC output buffer ON		-	-	50	pF
C_{SH}		Sample and hold mode		-	0.1	1	µF
V_{DAC_OUT}	Voltage on DAC_OUT output	DAC output buffer ON		0.2	-	V_{REF+} – 0.2	V
		DAC output buffer OFF		0	-	V_{REF+}	
$t_{SETTLING}$	Settling time (full scale: for a 12-bit code transition between the lowest and the highest input codes when DAC_OUT reaches final value ±0.5LSB, ±1 LSB, ±2 LSB, ±4 LSB, ±8 LSB)	Normal mode DAC output buffer ON CL ≤ 50 pF, RL ≥ 5 kΩ	±0.5 LSB	-	1.7	3	µs
			±1 LSB	-	1.6	2.9	
			±2 LSB	-	1.55	2.85	
			±4 LSB	-	1.48	2.8	
			±8 LSB	-	1.4	2.75	
		Normal mode DAC output buffer OFF, ±1LSB, CL = 10 pF		-	2	2.5	
t_{WAKEUP}(2)	Wakeup time from off state (setting the ENx bit in the DAC Control register) until final value ±1 LSB	Normal mode DAC output buffer ON CL ≤ 50 pF, RL ≥ 5 kΩ		-	4.2	7.5	µs
		Normal mode DAC output buffer OFF, CL ≤ 10 pF		-	2	5	
PSRR	V_{DDA} supply rejection ratio	Normal mode DAC output buffer ON CL ≤ 50 pF, RL = 5 kΩ, DC		-	-80	-28	dB

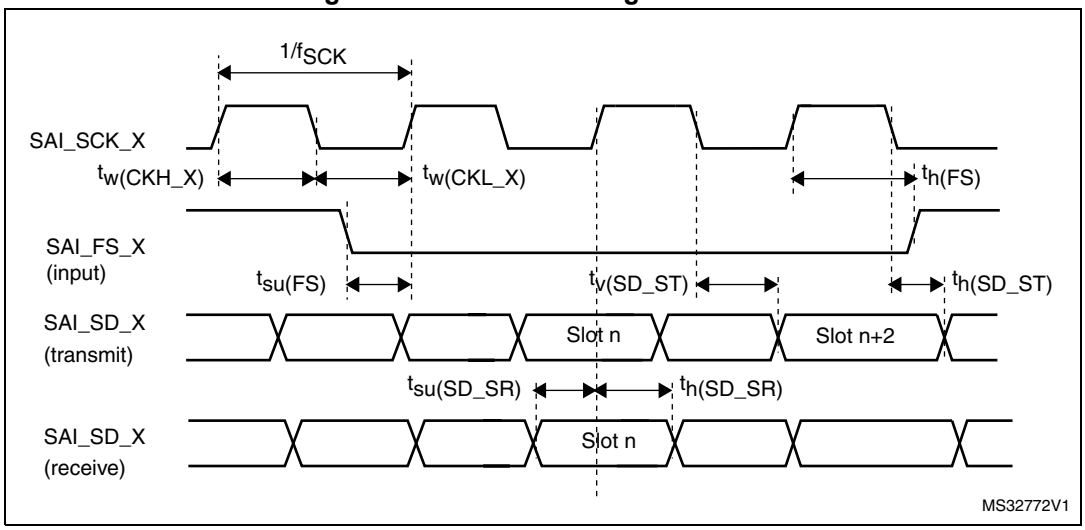
6.3.20 Comparator characteristics

Table 73. COMP characteristics(1)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage	-		1.62	-	3.6	V
V_{IN}	Comparator input voltage range	-		0	-	V_{DDA}	V
V_{BG}(2)	Scaler input voltage	-		V_{REFINT}			V
V_{SC}	Scaler offset voltage	-		-	±5	±10	mV
I_{DDA}(SCALER)	Scaler static consumption from V_{DDA}	BRG_EN=0 (bridge disable)		-	200	300	nA
		BRG_EN=1 (bridge enable)		-	0.8	1	µA
t_{START_SCALER}	Scaler startup time	-		-	100	200	µs
t_{START}	Comparator startup time to reach propagation delay specification	High-speed mode	$V_{DDA} \geq 2.7$ V	-	-	5	µs
			$V_{DDA} < 2.7$ V	-	-	7	
		Medium mode	$V_{DDA} \geq 2.7$ V	-	-	15	
			$V_{DDA} < 2.7$ V	-	-	25	
		Ultra-low-power mode		-	-	40	
t_D(3)	Propagation delay with 100 mV overdrive	High-speed mode	$V_{DDA} \geq 2.7$ V	-	55	80	ns
			$V_{DDA} < 2.7$ V	-	65	100	
		Medium mode		-	0.55	0.9	µs
		Ultra-low-power mode		-	4	7	
V_{offset}	Comparator offset error	Full common mode range	-	-	±5	±20	mV
V_{hys}	Comparator hysteresis	No hysteresis		-	0	-	mV
		Low hysteresis		-	8	-	
		Medium hysteresis		-	15	-	
		High hysteresis		-	27	-	
I_{DDA}(COMP)	Comparator consumption from V_{DDA}	Ultra-low-power mode	Static	-	400	600	nA
			With 50 kHz ±100 mV overdrive square signal	-	1200	-	
		Medium mode	Static	-	5	7	µA
			With 50 kHz ±100 mV overdrive square signal	-	6	-	
		High-speed mode	Static	-	70	100	
			With 50 kHz ±100 mV overdrive square signal	-	75	-	

1. Guaranteed by design, unless otherwise specified.

Figure 39. SAI slave timing waveforms



SDMMC characteristics

Unless otherwise specified, the parameters given in *Table 86* for SDIO are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 21: General operating conditions*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 11
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5 x V_{DD}

Refer to *Section 6.3.14: I/O port characteristics* for more details on the input/output characteristics.

Table 86. SD / MMC dynamic characteristics, V_{DD}=2.7 V to 3.6 V(1)

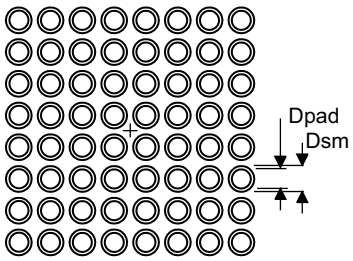
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PP}	Clock frequency in data transfer mode	-	0	-	50	MHz
-	SDIO_CK/fPCLK2 frequency ratio	-	-	-	4/3	-
$t_{W(CKL)}$	Clock low time	f_{PP} = 50 MHz	8	10	-	ns
$t_{W(CKH)}$	Clock high time	f_{PP} = 50 MHz	8	10	-	ns
CMD, D inputs (referenced to CK) in MMC and SD HS mode						
t_{ISU}	Input setup time HS	f_{PP} = 50 MHz	3.5	-	-	ns
t_{IH}	Input hold time HS	f_{PP} = 50 MHz	2.5	-	-	ns
CMD, D outputs (referenced to CK) in MMC and SD HS mode						
t_{OV}	Output valid time HS	f_{PP} = 50 MHz	-	12	13	ns
t_{OH}	Output hold time HS	f_{PP} = 50 MHz	10	-	-	ns
CMD, D inputs (referenced to CK) in SD default mode						
t_{ISUD}	Input setup time SD	f_{PP} = 50 MHz	3.5	-	-	ns
t_{IHD}	Input hold time SD	f_{PP} = 50 MHz	3	-	-	ns

Table 95. WLCSP64 - 64-ball, 3.141 x 3.127 mm, 0.35 mm pitch wafer level chip scale package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
b[3]	0.190	0.220	0.250	0.0075	0.0087	0.0098
D	3.106	3.141	3.176	0.1223	0.1237	0.1250
E	3.092	3.127	3.162	0.1217	0.1231	0.1245
e	-	0.350	-	-	0.0138	-
e1	-	2.450	-	-	0.0965	-
e2	-	2.450	-	-	0.0965	-
F	-	0.3455	-	-	0.0136	-
G	-	0.3385	-	-	0.0133	-
aaa	-	-	0.100	-	-	0.0039
bbb	-	-	0.100	-	-	0.0039
ccc	-	-	0.100	-	-	0.0039
ddd	-	-	0.050	-	-	0.0020
eee	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. Back side coating.
3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

Figure 55. WLCSP64 - 64-ball, 3.141 x 3.127 mm, 0.35 mm pitch wafer level chip scale package recommended footprint



WLCSP49_A04Z_FP_V1

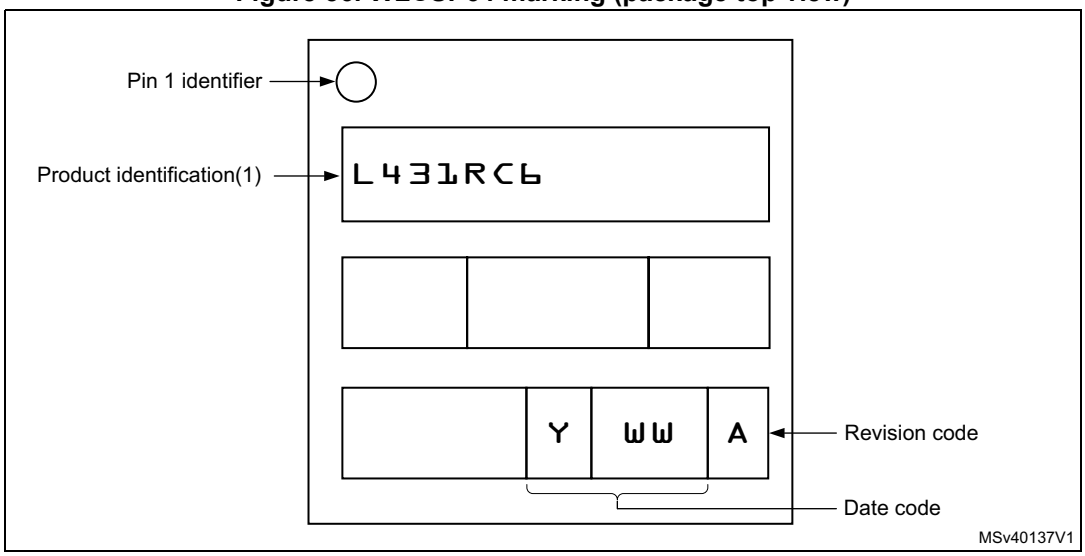
Table 96. WLCSP64 recommended PCB design rules (0.35 mm pitch)

Dimension	Recommended values
Pitch	0.35 mm
Dpad	0.210 mm
Dsm	0.275 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.235 mm
Stencil thickness	0.100 mm

Device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Figure 56. WLCSP64 marking (package top view)



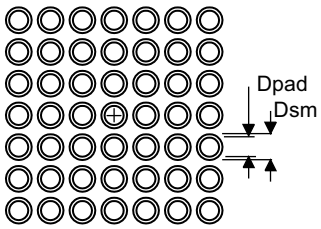
1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

Table 97. WLCSP49 - 49-ball, 3.141 x 3.127 mm, 0.4 mm pitch wafer level chip scale package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	-	0.175	-	-	0.0069	-
A2	-	0.380	-	-	0.0150	-
A3[2]	-	0.025	-	-	0.0010	-
b[3]	0.220	0.250	0.280	0.0087	0.0098	0.0110
D	3.106	3.141	3.176	0.1223	0.1237	0.1250
E	3.092	3.127	3.162	0.1217	0.1231	0.1245
e	-	0.400	-	-	0.0157	-
e1	-	2.400	-	-	0.0945	-
e2	-	2.400	-	-	0.0945	-
F	-	0.3705	-	-	0.0146	-
G	-	0.3635	-	-	0.0143	-
aaa	-	-	0.100	-	-	0.0039
bbb	-	-	0.100	-	-	0.0039
ccc	-	-	0.100	-	-	0.0039
ddd	-	-	0.050	-	-	0.0020
eee	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. Back side coating
3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

Figure 58. WLCSP49 - 49-ball, 3.141 x 3.127 mm, 0.4 mm pitch wafer level chip scale package recommended footprint



WLCSP49_A04Z_FP_V1

7.10 Thermal characteristics

The maximum chip junction temperature ($T_J$max) must never exceed the values given in *Table 21: General operating conditions*.

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

$$T_J \text{ max} = T_A \text{ max} + (P_D \text{ max} \times \Theta_{JA})$$

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

$P_{I/O}$ max represents the maximum power dissipation on output pins where:

$$P_{I/O} \text{ max} = \Sigma (V_{OL} \times I_{OL}) + \Sigma ((V_{DDIOx} - V_{OH}) \times I_{OH}),$$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 102. Package thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	**Thermal resistance junction-ambient** UFQFPN48 - 7 × 7 mm / 0.5 mm pitch	33	°C/W
	Thermal resistance junction-ambient LQFP48 - 7 × 7 mm / 0.5 mm pitch	57	
	Thermal resistance junction-ambient WLCSP49 3.141 x 3.127 / 0.4 mm pitch	48	
	Thermal resistance junction-ambient LQFP64 - 10 × 10 mm / 0.5 mm pitch	46	
	Thermal resistance junction-ambient UFBGA64 - 5 × 5 mm / 0.5 mm pitch	65	
	Thermal resistance junction-ambient WLCSP64 3.141 x 3.127 / 0.35 mm pitch	46	
	Thermal resistance junction-ambient LQFP100 - 14 × 14 mm / 0.5 mm pitch	42	
	Thermal resistance junction-ambient UFBGA100 - 7 × 7 mm / 0.5 mm pitch	57	

7.10.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org